

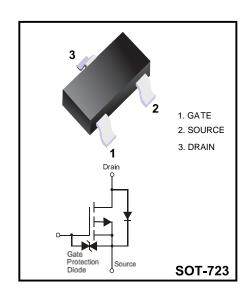
P-Channel MOSFET

Features

- Lead Free Product is Acquired
- Surface Mount Package
- P-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive

Application

- Load/Power Switching
- Interfacing, Logic Switching
- Battery Management for Ultra Small Portable Electronics



Marking Code		
YFW3139K	KD	

V _{(BR)DSS}	R _{DS(on)} MAX	I _D
	520mΩ@-4.5V	
-20V	700mΩ@-2.5V	-0.66A
	950mΩ(TYP)@-1.8V	

Absolute Maximum Ratings (Ta=25℃)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Typical Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current (note 1)	I _D	-0.66	А
Pulsed Drain Current (t _p =10 μ s)	I _{DM}	-1.2	Α
Power Dissipation (note 1)	P _D	150	mW
Thermal Resistance from Junction to Ambient (note 1)	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T _{STG}	-55~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10 s)	TL	260	°C



Electrical Characteristics (Ta=25℃ unless otherwise specified.)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	V (BR)DSS	V _{GS} = 0V, I _D =-250µA	-20			V
Zero gate voltage drain current	IDSS	V _{DS} =-20V,V _{GS} = 0V			-1	μΑ
Gate-body leakage current	Igss	V _{GS} =±10V, V _{DS} = 0V			±20	μA
Gate threshold voltage (note 2)	VGS(th)	V _{DS} =V _{GS} , I _D =-250μA	-0.35	-0.45	-1.1	V
Drain-source on-resistance (note 2)		Vgs =-4.5V, ID =-1A		430	520	mΩ
	R _{DS} (on)	VGS =-2.5V, ID =-0.8A		624	700	mΩ
		Vgs =-1.8V, ID =-0.5A		950		mΩ
Forward transconductance (note 2)	gFS	V _{DS} =-10V, I _D =-0.54A		1.2		S
Diode forward voltage	V _{SD}	I _S =-0.5A, V _{GS} = 0V			-1.2	V
DYNAMIC CHARACTERISTICS (note 4	1)		•		•	
Input capacitance	C _{iss}	V _{DS} =-16V,V _{GS} =0V,f =1MHz		113	170	pF
Output capacitance	Coss			15	25	pF
Reverse transfer capacitance	C _{rss}			9	15	pF
SWITCHING CHARACTERISTICS (not	e 4)					
Turn-on delay time (note 3)	td(on)			9		ns
Turn-on rise time (note 3)	tr	V _{GS} =-4.5V,V _{DS} =-10V,		5.8		ns
Turn-off delay time (note3)	td(off)	$I_D = -200 \text{mA}, R_{GEN} = 10 \Omega$		32.7		ns
Turn-off fall time (note 3)	tf]		20.3		ns

Notes:

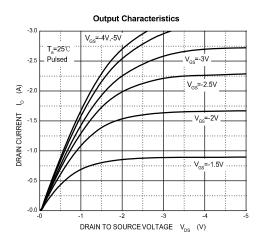
- 1. Surface mounted on FR4 board using the minimum recommended pad size.
- 2. Pulse Test : Pulse Width=300µs, Duty Cycle=2%.
- 3. Switching characteristics are independent of operating junction temperatures.
- 4. Guaranteed by design, not subject to producting.

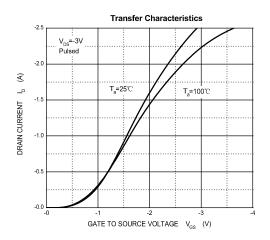
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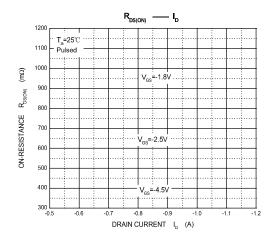
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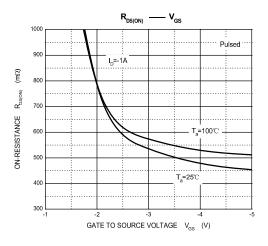


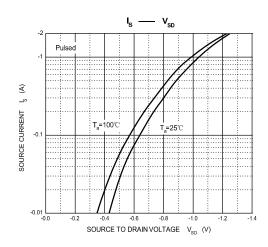
Typical Characteristics

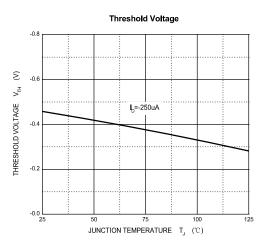












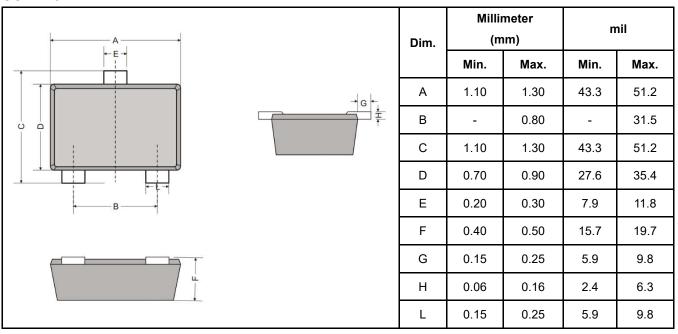


Ordering information

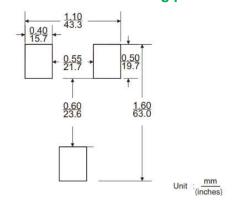
Package	Packing Description	Base Quantity	Packing Quantity
SOT-723	Tape/Reel,7"reel	8000pcs/Reel	64000PCS/Box 320000PCS/Carton

Package Dimensions

SOT-723



The recommended mounting pad size





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